

BF506

**CASE 29-03, STYLE 17
TO-92 (TO-226AA)**

VHF TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

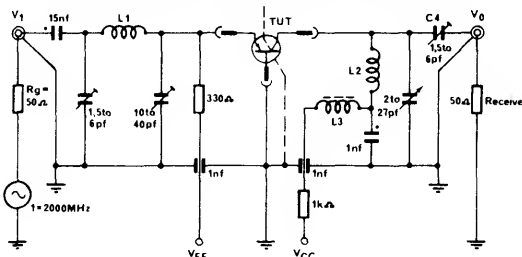
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current - Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 5.0 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	35	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	4	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ V}, I_E = 0$)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 3 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)	h_{FE}	20	—	—	
SMALL SIGNAL CHARACTERISTICS					
Current-Gain - Bandwidth Product ($I_C = 1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz}$)	f_T	400	600	—	MHz
Collector-Base Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C_{CBO}	—	0.6	0.9	pF
Feedback Capacitance (Grounded Base) ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C_{rb}	—	0.15	0.25	pF
Noise Figure ($I_C = 1 \text{ mA}, R_S = 50 \Omega, f = 200 \text{ MHz}, V_{CC} = 6 \text{ V}$)	Nf	—	2.5	4	dB
Power Gain ($I_C = 3 \text{ mA}, R_L = 1 \text{ K}\Omega, f = 200 \text{ MHz}, V_{CC} = 10.8 \text{ V}$)	G_{pb}	14	22	—	dB

200 MHz POWER GAIN NOISE FIGURE TEST CIRCUIT

*Leadless ceramic disc capacitor
L1 - 3 turns 0.0 mm enamel, 4 mm dia
L2 - 2 turns 1 mm enamel, 6.5 mm dia

FIGURE 1 – CURRENT GAIN – BANDWIDTH PRODUCT

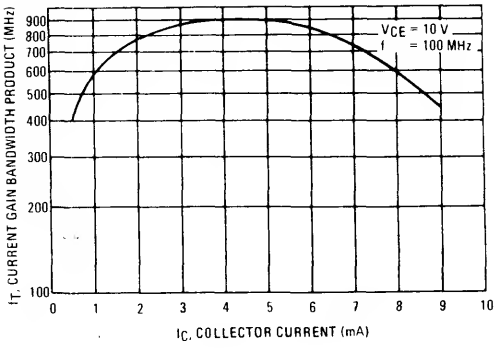


FIGURE 2 – NOISE FIGURE

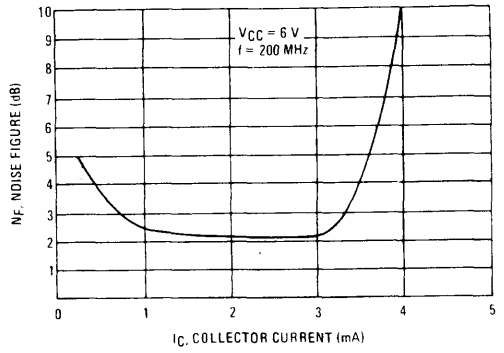


FIGURE 3 – FORWARD TRANSFER ADMITTANCE

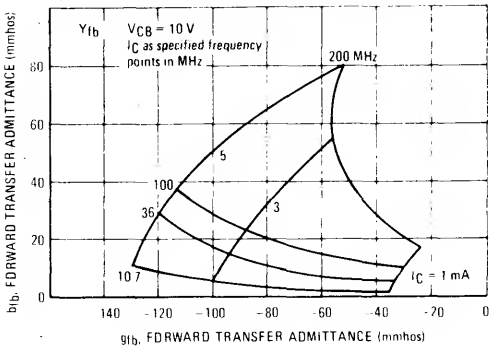


FIGURE 4 – INPUT ADMITTANCE

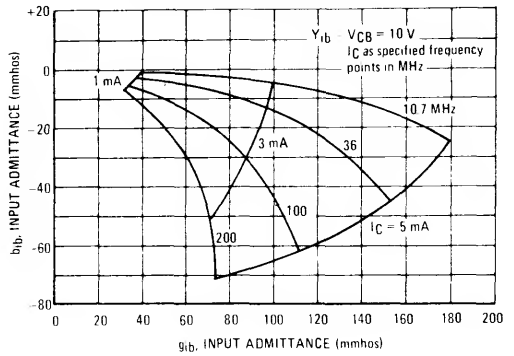


FIGURE 5 – OUTPUT ADMITTANCE

